



For the two given spectral lines,  $A_1, A_2, g_1, g_2, \lambda_1, \lambda_2, E_1, E_2$  and  $k$  are all constants. When the relative intensities,  $I_{\lambda_1}$  and  $I_{\lambda_2}$ , are obtained, the SCB plasma temperature can be derived from Equation (2). The effect of the spectral radiance and spectral transmissivity on the spectral measurement decreases, especially when the interval of two spectral lines is very small. In this paper, the two spectral lines were Cu I 510.5 and Cu I 521.8 nm.

The measurement system consisted of two different wavelength interference filter, two photo-multiplier detectors (R300), a fast responding circuit, a data-acquisition card and a 486 PC. The diagram of measurement system is shown as Fig. 1.

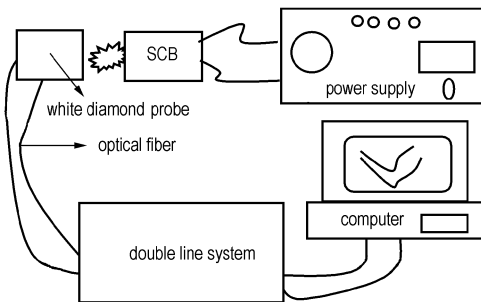


Fig. 1 The diagram of measurement system

## 2.2 The SCB

The SCB heavily  $n$ -type dopant concentration is about  $1 \times 10^{20}$  phosphorus atoms/cm<sup>3</sup>. The size is 100  $\mu\text{m}$  long by 400  $\mu\text{m}$  wide by 2 – 3  $\mu\text{m}$  thick. Its resistance about 1  $\Omega$  is designed for considering the electrostatic safety. Its typical structure is an "H"-shaped thin poly-silicon-on-silicon film with two Al lands for electrical contacts, as shown in Fig. 2.

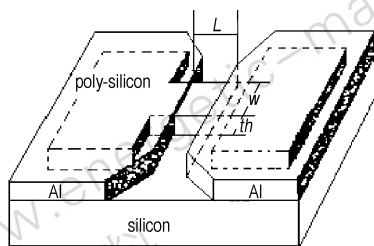


Fig. 2 The diagram of SCB structure

The apparatus is mounted on a solid insulator (ceramic), which insulates the SCB from the main housing of the ignition unit. It should be noticed that the SCB materials contains a few copper, which is critical for this measurement method. And it is different in volume and dopant concentra-

tion from the one Benson<sup>[1]</sup> and Jongdea Kim<sup>[10]</sup> adopted.

## 2.3 Experimental process

A firing set selected in the experiment consisted of a capacitor (68  $\mu\text{F}$ ) and a power supply. With it, the bridge materials were heated by electricity. The bridge melted down firstly, and then vaporized. Once the bridge materials were vaporized completely, the current flowed through the vapor, producing the plasma discharge called the late-time discharge (LTD). In this test the SCB discharged to room air directly and a white light was observed with an audible "pop". The relative intensity of the double line of Cu-atomic emission ( $I_{\lambda_1}, I_{\lambda_2}$ ) from the SCB plasma was detected by photo-multiplier, through which the optical signal was transformed to electrical signal. Then the obtained signals were stored in computer for further analysis.

## 3 Results and discussions

The experimental results obtained under the conditions are given in Table 1.

Table 1 Experimental conditions and results

group	power supply/V	capacitor/ $\mu\text{F}$	plasma life time/ $\mu\text{s}$	temperature/K
1	24	68	170.7	1790 – 2710
2	25	68	198.9	1730 – 3260
3	27	68	207.3	1790 – 3390
4	30	68	211.4	1750 – 3480
5	32	68	283.4	1770 – 3880

The processing of the third group of data is taken as an example to describe how the results were obtained. The experiment was carried out under the condition of a given power supply (30 V) and capacitance (68  $\mu\text{F}$ ). Fig. 3 shows the signal obtained from the double line of the system.

Because the measurement system recorded the SCB plasma light, the signal could be treated as the onset of the late-time discharge (LTD). The curve in Fig. 4 shows the time evolution of the SCB plasma temperature, which illustrate that the SCB plasma temperature increases from 1750 K to 3480 K during the period of 211.4  $\mu\text{s}$ .

Other data were processed in the same way. It can be concluded that the highest SCB plasma temperature increases with the rise of the input energy. And the same tendency can be seen in the duration of the SCB plasma. The SCB plasma temperature in every test at the onset of the late-time

discharge (LTD) was similar, being 1750 K approximately. The main component of the SCB was silicon. The SCB size was about  $2\ \mu\text{m} \times 100\ \mu\text{m} \times 400\ \mu\text{m}$ , and Si-atoms was approximately  $4 \times 10^{15}$ . The SCB was doped with a concentration of about  $1 \times 10^{20}$  phosphorus atoms/ $\text{cm}^3$ , so there were about  $8 \times 10^{12}$  phosphorus atoms in SCB. Due to the influence of phosphorus atoms, the vaporization temperature of the SCB was lower than that of pure silicon (2628 K).

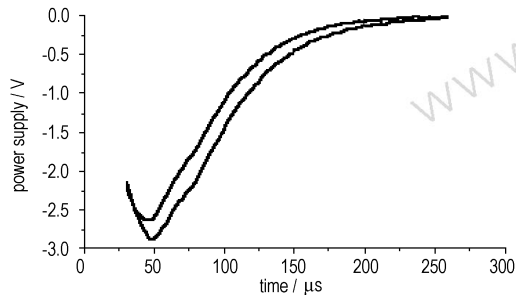


Fig. 3 Time evolution of relative intensities ( $I$ ) of two copper lines

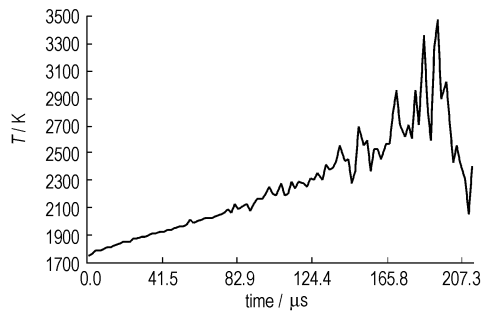


Fig. 4 Time evolution of the SCB plasma temperature

## 4 Conclusions

The temporal resolution of the system is  $0.1\ \mu\text{s}$ , which is suitable for measuring instant SCB plasma temperature. Moreover, the time evolution of the SCB plasma temperature can be obtained from this system. The SCB discharge was comprehended more economically and easily. The following conclusions can be drawn: (1) The onset of the late time discharge (LTD) of the SCB plasma temperature is about 1750 K, which has little relationship with the input energy. (2) In each late-time discharge (LTD) of the SCB, the temperature increases with the time evolving. (3) The highest temperature and duration of the SCB plasma are closed related to the input energy. They increase with the increasing of the input energy.

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## Effects of the Binding Agents on the Burning Rate of the Tungsten Delay Composition

XU Jun-feng, PENG Jia-bin, WANG Xiu-zhi, ZHANG Zhou-mei, ZHANG Ye

(Shann-xi Applied Physics-Chemistry Institute, Xi'an 710061, China)

**Abstract:** To study the effects of the binding agents on the burning rate of the tungsten delay composition, two delay compositions in bound form were made with nitrocellulose and Teflon separately. An experiment on the two delay compositions was carried out and their delay time at room temperature and high temperatures (120, 160, 180 °C) were obtained. The results show that the burning rate of the composition with nitrocellulose as binding agent is much faster than that of the composition with Teflon as binding agent. When the temperature rises, the burning rate of the composition with nitrocellulose as binding agent increase rapidly while the burning rate of the composition with Teflon as binding agent does slowly.

**Key words:** applied chemistry; delay composition; tungsten type delay composition; binding agent; burning rate

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## 原子发射光谱双谱线法测量半导体桥 (SCB) 等离子体温度

冯红艳, 李艳, 张琳, 吴蓉, 王俊德, 朱顺官

(南京理工大学化工学院, 江苏南京 210094)

**摘要:** 在原子发射光谱双谱线法的基础上, 设计了含有两个干涉滤光片和光电倍增管双谱线测温系统。仪器的最高的时间分辨率为 0.1  $\mu\text{s}$ 。讨论了不同能量输入条件下 SCB 等离子体的温度和等离子体的存在时间。实验结果表明在电压 24 ~ 32 V, 电容 68  $\mu\text{F}$  不变的情况下, 等离子体的温度从 2710 K 升高到 3880 K, 等离子体存在时间从 170.7  $\mu\text{s}$  上升到 283.4  $\mu\text{s}$ 。

**关键词:** 应用化学; SCB 等离子体; 原子发射光谱法; 温度测定

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 LI Jian-chuan, HU Niao-qing, QIN Guo-jun, et al. Application and construction of bayesian networks based on fault trees[J]. *Computer Engineering & Application*, 2003, 24: 225 - 228.

## Safety Fault Analysis of Igniter Based on FTA and BN

HU Yan-chen<sup>1,2</sup>, WANG Pei-lan<sup>1</sup>, ZHENG Heng<sup>3</sup>, LI Hao<sup>2</sup>

(1. State Key Laboratory of Explosion Science and Technology, Beijing Institute of Technology, Beijing 100081, China;

2. PLA Military Representative Office in No. 474 Factory, Fushun 113003;

3. School of Management and Economics, Beijing Institute of Technology, Beijing 100081, China)

**Abstract:** Bayesian networks(BN) and fault tree analysis(FTA) were compared for safety fault analysis. According to the initiator system, a new method that used FTA & BN to perform fault analysis was proposed. The reasons causing safety fault to the igniter with the method were analyzed as the non-uniform density of delay powder, the sticking of protechnic charge to the internal wall of delay tube and the failure of alarm device, etc. The corresponding solution was established at end.

**Key words:** safety engineering; initiators; igniter; fault analysis; bayesian networks (BN); fault tree analysis (FTA)